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(54) Title: METAL-DOPED CARBON HARDMASKS

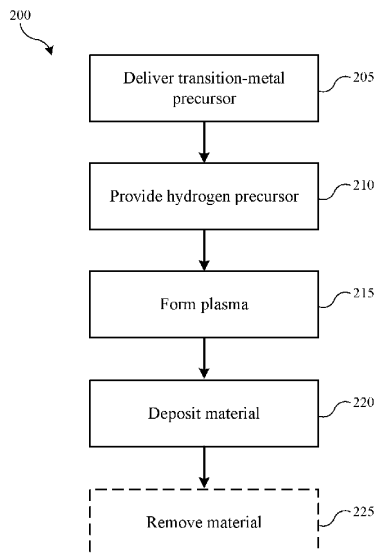


FIG. 2

(57) Abstract: Exemplary deposition methods may include delivering a ruthenium-containing precursor and a hydrogen-containing precursor to a processing region of a semiconductor processing chamber. At least one of the ruthenium-containing precursor or the hydrogen-containing precursor may include carbon. The methods may include forming a plasma of all precursors within the processing region of a semiconductor processing chamber. The methods may include depositing a ruthenium-and-carbon material on a substrate disposed within the processing region of the semiconductor processing chamber.

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